

SW Test Workshop Semiconductor Wafer Test Workshop

A Full-Automatic Test System for Characterizing Large-Array Fine-Pitch Micro-Bump Probe Cards Erik Jan Marinissen Jörg Kiesewetter **Eric Hill Ferenc Fodor Ken Smith** Bart De Wachter **Cascade**Microtech® unec A FORMFACTOR COMPANY Leuven, Belgium Thiendorf, Germany Beaverton, OR, USA June 4-7, 2017

I.INTRODUCTION Direct Micro-Bump Probing

- Functional interconnects of 3D-stacked dies are formed by large arrays of fine-pitch micro-bumps
- Impossible to probe with conventional probe technology
 - Cantilever probes : cannot handle arbitrary arrays
 - Vertical probes : cannot handle the fine pitch
- Options for pre-bond test
 - I. Skip pre-bond test: poor compound stack yield; higher cost
 - 2. Dedicated pre-bond probe pads: extra design, area, test time, post-bond load; and micro-bumps remain untested

Use advanced probe technology to probe micro-bumps







5

3D-T



micro-bumps -

Related Prior Work

- SWTW'II: Marinissen et al. (imec + Cascade Microtech)
 Imec and Cascade started collaboration, defined probe targets
- ITC'II: Smith et al. (Cascade Microtech + imec)
 First collaboration results, mainly on probe technology
- SWTW'I3: Böhm et al. (Feinmetall + Team Nanotec + imec + FH + CM) Silicon crown tips, embedded in vertical probe card with TSVs Most Inspirational Presentation Award, but no product follow-up
- ITC'I4: Marinissen et al. (imec + Cascade Microtech + TU Delft)
 - WIOI-IBank: good R_c ; no impact on bond yield; cost-effective
 - But... (i) only I Bank and (ii) only daisy-chains of 30 micro-bumps







- I. Introduction
- 2. Wide-I/O Micro-Bump Arrays
- 3. Vortex-2 Test System
- 4. Probe Technology
- 5. Test System Software
- 6. Experimental Results
- 7. Test Cost Comparison
- 8. Conclusion



2. WIDE-I/O MICRO-BUMP ARRAYS What Do We Want To Probe?

Micro-Bump Probe Targets

- imec's PoR @40µm pitch
- Today's advanced industry practice
 Wide-I/O Micro-Bump Arrays
- WIO1: 1,200 micro-bumps @50/40µm pitch
- WIO2: 1,752 micro-bumps @40/40µm pitch



25µm

Top

40um

Bottom

15µm

5µm

1µm 3.5µm

25µm

5µm

Ø25µm Cu

CII

25µm

Ø15µm Cu/Ni/Sn

JEDEC STANDARD

Mr 102 (Widebo

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3.VORTEX-2 TEST SYSTEM Vortex-2 Test System





3.VORTEX-2 TEST SYSTEM Vortex-2: In-Line in imec's Fab-2





3.VORTEX-2 TEST SYSTEM Cascade Microtech CM300 Probe Station

- Wafer Handling
 - Full-automatic wafer loader (200/300mm)
 - Manual loading of tape frames
- Thermal Control System: -60...+200 °C
- Four Cameras
 - (1) eVue ↓ (3) Chuck 1
 (2) Platen ↓ (4) ContactView ™ →
- Platen Camera.
- Microscope Bridge Removed for Test Head
 - Probe alignment with Platen and Chuck cameras only
 - Chuck needs to move between 'Align' and 'Probe' positions











3. VORTEX-2 TEST SYSTEM

National Instruments Semiconductor Test System





- PXI Rack: programmable Switch Matrix
 - 4 input rows driven by DMM
 - 9×136 = 1,224 output columns
- Two and four-point R measurements



3.VORTEX-2 TEST SYSTEM Grounding the FET-Based Switch Matrix

- Wide-I/O Switch Matrix is composed of nine concatenated switch modules
 - 9×(4×136)= 4 rows × 1,224 columns
- NI's PXI-2535 FET-based SMX
 - Benefits
 - Low cost and unlimited life-time
 - All 544 switches can be "on"
 - Drawbacks
 - Significant leakage current
 - Charge injection during power-up



but leaves fix to user We suggested programmable GND

- as feature in new NI SMX modules
- For now, we implemented aprog'able GND from probe card into SMX



3. VORTEX-2 TEST SYSTEM

Measurement Routines and Parasitics





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4. PROBETECHNOLOGY Pyramid[®] Rocking Beam Interposer Probe Cores







4. PROBETECHNOLOGY From Core-I/O to Probe Tip



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5. TEST SYSTEM SOFTWARE Automatic Test Generation Inputs

- Test System Description look-up table
 - Per line : probe number; core-I/O;
 - Example: 3;



- Probe Core Description
 - Key parameters, incl. probes layout and recommended/max OT

IMEC-36
WIO2-1ch
1
6
73
40
150
150
0
0

SH02;

pogo block/pin; switch matrix/column S13_H08; SMX5_COL14





PROBE	CORE IO	POGO PIN	SMX_COL
1	WH23	\$19_G05	SMX7_COLI13
2	SD02	\$13_M06	SMX5_COL86
3	SH02	\$13_H08	SMX5_COLI4
4	SD03	\$13_M05	SMX5_COL90
5	SH03	\$13_H07	SMX5_COLI0
6	SD04	\$13_M04	SMX5_COL94
7	SH04	\$13_H06	SMX5_COL6
8	SD05	\$13_M03	SMX5_COL98
9	SH05	\$13_H05	SMX5 COLLID
10	SD06	SI3 MOD	
	SH06		



5. TEST SYSTEM SOFTWARE

Many Test Results: Data Abstraction & Visualization



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imec Test Chip Designs with Micro-Bumps

BMB: Blanket Micro-Bump

- All micro-bumps shorted by blanket Cu
 - Arrays: 50/50µm pitch, WIOI, WIO2
 - Banks with 0/1/2 dummy rings
- 9,421,272 functional micro-bumps/wafer





Vesuvius-2.5D

WIO1: 1,200 bumps



40 daisy-chains of 30 micro-bumps each

PTCU/W: Processing Test Chips

- WIO2 I bank: 438 micro-bumps
- Embedded micro-bumps: zero height
- Micro-bumps pairwise connected through MI in diagonal fashion





Incoming Inspection on Blanket Wafer

- Increase over-travel from 0 to OT_{max}
- Perform 'Probe Check' routine: for all probes p∈P do { two-point R measurement p vs. P\{p} 60 }
- Determine
 - Open probes, if any: R > R_{MAX}
 - FtL: First-to-Last OT; here 40µm
 - Recommended OT; here 100µm
 - Too low: poor contact
 - Too high: reduced lifetime





6. EXPERIMENTAL RESULTS Probe Tip Cleaning

- Recommended cleaning set-up
 - Substrate : ITS Probe Lapping Film, I µm grit particle size
 - Recipe : 60% of probing over-travel, 10 touch-downs
 - Interval :After 50 touch-downs



Before Tip Cleaning





Contact Resistance Dependent on Bump Metallurgy



- Sample size: 20,900 37,620 measurements per wafer
- Pass/Fail threshold $R_{\rm TH}$ set at 50 Ω
- Large variation: due to parasitic R in test system and probe core
- Small variation: micro-bump metallurgy
 - D05: Cu
 - D09: Ni
 - **D02:** Co
 - DI4: Cu +20nm NiB
 - D09: Cu +40nm NiB

Probe-To-Pad Alignment (PTPA) Accuracy

- **PTPA Accuracy**: determined by (1) probe station and (2) probe core
 - Measure probe-mark errors in all four corners of micro-bump array

I. Probe Station Accuracy 🔲



- Equals error of BL probe mark, as BL tip is main probe training location
- Error is chuck-position dependent

2. Probe Core Accuracy

- Translate errors such that BL= (0,0)
- Errors other corners due to probe core
- These errors are chuck-pos independent





Probe Station's PTPA Results

- Cannot Use Top-View Camera
 - No microscope bridge
 - Probe cores 'non see -through'

Platen + Chuck Cameras Only

- Align' ↔ 'Probe': chuck moves
- Rely on Compensation Matrix
- Compensation Matrix recalibrated in Jan and May 2017

Thermal Control required for accurate PTPA









Stage Test Platen Cam After Service May 2017





(2 µm, 4 µm]

0

-

Probe Cores' Grid Accuracy Results

• WIO2-I Bank

0

0



• WIOI-4Bank



Cor-	ldeal (µm)		Actual (µm)		Error (µm)		Relative Error	
ner	x	у	x	у	x	у	x	у
BL	0.00	0.00	0.00	0.00	0.00	0.00	0.00%	0.00%
BR	5250.00	0.00	5253.93	-0.99	3.93	-0.99	0.07%	-0.19%
TR	5250.00	520.00	5255.65	516.86	5.65	-3.14	0.11%	-0.60%
TL	0.00	520.00	1.13	516.58	1.13	-3.42	0.02 %	-0.66%



6. EXPERIMENTAL RESULTS Probe Marks on Various Micro-Bumps at 40µm Pitch





6. EXPERIMENTAL RESULTS Probe Mark Impact on Stack Interconnect Yield

- Probe Marks
 - On Cu, Co, Ni: very small
 - On Sn: can be reflowed away

WIOI Bank	Α	В	С	D
Top die probed	×	\checkmark	\checkmark	×
Bottom die probed	\checkmark	\checkmark	×	×
Interconnect yield	100%	100%	100%	100%
DC resistance R _{dc}	32.0 Ω	42.4 Ω	45.0 Ω	33 .ΙΩ



Experiment on Vesuvius-2.5D with WIOI-4Banks

- Probed per bank in all four combinations of top/bottom die yes/no probed prior to stacking
- No impact on stack interconnect yield observed [Marinissen et al. – ITC'14]

Ch.	DC	Stack 1	Stack 2	Stack 3	Stack 4	Stack 5	Stack 6	Stack 7	Stack 8
А	1	24.8	25.2	25.7	29.3	31.7	34.7	38.7	30.9
А	2	29.7	36.6	37.6	41.0	40.6	106.0	34.7	35.2
А	3	24.7	25.7	27.0	30.5	25.2	25.2	26.3	30.1
А	4	25.8	26.4	27.4	27.6	26.9	27.2	27.6	26.9
А	5	24.0	23.7	25.0	25.0	24.1	26.5	28.1	28.1
А	6	29.4	29.1	30.3	32.3	30.5	33.5	33.7	33.7
А	7	26.8	28.1	27.7	27.6	28.0	27.2	27.9	27.6
А	8	30.4	29.9	32.9	32.1	32.0	32.4	32.1	31.9
А	9	38.2	35.2	40.6	39.1	46.3	42.2	41.6	42.4
А	10	34.3	30.1	33.3	33.3	33.5	35.2	34.7	37.2
В	1	36.3	26.4	39.3	39.4	43.0	46.0	53.7	42.0
В	2	51.3	31.2	44.4	50.3	51.4	53.1	47.3	46.9
В	3	35.8	37.6	38.7	40.4	36.8	36.8	37.5	37.3
В	4	36.8	38.0	39.2	39.6	38.3	39.0	39.5	38.6
В	5	35.3	34.9	36.5	36.5	35.9	36.6	38.7	36.8
В	6	40.4	40.2	43.4	44.1	42.2	44.0	44.8	44.4
В	7	37.9	39.8	39.6	39.3	39.1	38.7	39.8	39.3
В	8	41.5	41.5	44.9	44.2	43.6	43.8	44.5	43.4
В	9	48.2	47.9	51.8	51.5	53.7	54.3	52.9	53.5
В	10	51.1	41.8	44.6	46.1	46.9	51.3	46.3	45.1
С	1	58.4	51.8	78.6	73.5	59.4	98.9	56.0	52.2
С	2	46.5	43.2	44.6	47.4	48.0	49.7	49.4	46.4
С	3	40.0	37.7	41.3	41.1	41.3	41.1	42.7	38.9
С	4	45.1	44.7	49.1	48.2	50.7	51.1	50.0	49.5
С	5	41.0	39.6	43.4	42.6	42.1	41.7	42.4	41.5
С	6	37.5	38.5	38.8	38.8	38.7	38.4	39.0	38.4
С	7	41.1	41.0	42.9	43.6	48.5	44.8	45.3	45.2
С	8	36.9	37.1	38.5	38.2	44.5	38.1	40.1	38.4
С	9	40.0	41.0	42.7	42.4	41.7	41.9	42.4	41.8
С	10	40.2	42.7	42.5	45.3	45.8	40.8	41.5	40.6
D	1	38.4	53.4	67.0	64.5	53.4	62.3	47.8	41.4
D	2	32.4	29.7	32.4	35.4	36.9	35.2	35.9	34.6
D	3	29.5	26.9	29.2	29.0	29.9	30.8	29.5	31.6
D	4	30.8	33.4	38.0	37.5	38.3	39.6	38.3	38.5
D	5	29.8	29.5	31.2	30.7	40.4	30.2	30.5	30.4
D	6	26.1	26.2	27.0	27.9	26.6	26.6	27.1	26.9
D	7	30.1	30.7	30.9	31.8	31.2	33.0	34.7	33.8
D	8	25.7	25.5	26.7	26.5	26.7	26.5	27.5	27.4
D	9	29.5	29.7	30.7	31.0	29.7	30.6	30.4	30.2
D	10	28.8	30.0	31.1	30.7	30.5	30.9	29.9	29.1



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7. TEST COST COMPARISON

Cost Modeling for Single-Site Testing

Cost Comparison

- Case:Vesuvius-2.5D
- Two active dies on top of passive interposer



Three Scenarios

- I. No pre-bond test
- 2. Extra pre-bond pads 📕
- 3. Micro-bump probing

Payamatak	Inter-	I. No Pre-Bond	2. Extra Pads	3. Bump Probe
	poser	Dies I+2	Dies I+2	Dies I+2
Pre-bond test contacts / die	n.a.	n.a.	only I 20	I,200
300mm wafer cost	\$ 700	\$ 3,000	\$ 3,000	\$ 3,000
Die area	200 mm ²	65.61 mm ²	6 <mark>6</mark> .61 mm²	65.61 mm ²
Gross die / wafer	302	968	9 <u>53</u>	968
Defect density	0.1 /cm ²	0.0-1.0 /cm ²	0.0-1.0 /cm ²	0.0-1.0 /cm ²
Die yield	84.52%	100-65.76%	100-65. <u>48</u> %	100-65.76%
Pre-bond fault coverage	n.a.	<u>0</u> %	99 %	99%
Pre-bond test time / die	n.a.	<u>0</u> s	<u>100</u> s	10 s
Pre-bond probe card cost / die	n.a.	0	0	\$ 0.50
Pre-bond test cost/die	n.a.	\$ 0.00	\$ 5.00	\$ 1.00
Stack interconnect yield	100%	99 %	99%	9 <u>8</u> % ?
Final fault coverage	100%	99%	99%	99%
Final test time / die	ls	10 s	10 s	10 s



7. TEST COST COMPARISON 3D-COSTAR Cost Modeling Results

- I. No Pre-Bond Test Only acceptable if pre-bond die yield is high
- 2. Extra Pre-Bond Pads 10× test time increase ⇒ test significant cost-add
- 3. Micro-Bump Probing expensive advanced probe card is minor overall cost contributor No difference in product

quality due to Final Test!





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- Unique system for large-array fine-pitch micro-bump probing based on Cascade Microtech CM300
 - At imec routinely used for micro-bump arrays @40/50µm pitch
 - Temperature control and good calibration required
 - PTPA $\leq \pm 2.5 \mu$ m: appears sufficient even for 20 μ m-pitch micro-bumps
- Cascade Microtech Pyramid[®] RBI probe cards/cores
 - Advanced MEMS-based thin-film probe technology
 - Large arrays down to 40µm pitch
 - Contact resistance 0.1-2.0 Ω ; parasitic resistance in space transformer ~5 Ω
 - Low force \Rightarrow Limited probe mark \Rightarrow No impact on stacking yield observed



8. CONCLUSION

2-0-1-7

Challenges and Solutions for Micro-Bump Probing

SolutionsAdvanced MEMS-type probe cards
Accurate, thermally-stable prober
Large #channels; hard-docking
 Automated data visualization
 Parasitics, over-travel, tip cleaning
Dependent on bump metallurgy
Low-force probe cards
Reflow for soft Sn micro-bumps
 Advanced probes are expensive
 But alternatives are more expensive

8. CONCLUSION Acknowledgments

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